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L13: Entry 1 of 1

File: DWPI

Jul 19, 2001

DERWENT-ACC-NO: 2001-627381

DERWENT-WEEK: 200173

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TITLE: Thermal vacuum vaporization apparatus comprises a vacuum chamber assembly with a plasma etching-vacuum chamber, a chamber for vaporizing the organic layer and a chamber for vaporizing the metallic layer

PATENT-ASSIGNEE: PRECISION INSTR DEV CENT NAT SCI CO (PRECN)

PRIORITY-DATA: 2001DE-2006283 (April 10, 2001)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
DE <u>20106283</u> U1	July 19, 2001		019	C23C014/24

APPLICATION-DATA:

PUB-NO	APPL-DATE	APPL-NO	DESCRIPTOR
DE 20106283U1	April 10, 2001	2001DE-2006283	

INT-CL (IPC): C23 C 14/24

ABSTRACTED-PUB-NO: DE 20106283U

BASIC-ABSTRACT:

NOVELTY - Thermal vacuum vaporization apparatus comprises a vacuum chamber assembly (1) formed as a connecting body of the plasma etching-vacuum chamber (1A), the chamber (1B) for vaporizing the organic layer and the chamber (1C) for vaporizing the metallic layer. The chamber (1B) and the chamber (1C) are emptied using a pump system (2) to form a vacuum.

DETAILED DESCRIPTION - Preferred Features: A sample holder (3a5) is inserted by a magnetic slide rod (3a1) into the plasma etching-vacuum chamber and further into the chamber (1B). The holder is transferred on the sample seat (3b4) of the rod.

The three chambers (1A, 1B, 1C) are integrated in one body using high vacuum valves (11, 12).

USE - Used for organic electroluminescent diodes.

ADVANTAGE - The vaporization processes are simplified.

DESCRIPTION OF DRAWING(S) - The drawing shows a side view of the thermal vacuum vaporization apparatus.

Vacuum chamber assembly 1

Plasma etching-vacuum chamber 1A

chamber for vaporizing the organic layer 1B

Chamber for vaporizing the metallic layer 1C

Pump system 2

Slide rod 3a1

Sample holder 3a5

Sample seat 3b4

ABSTRACTED-PUB-NO: DE 20106283U

EQUIVALENT-ABSTRACTS:

CHOSEN-DRAWING: Dwg.1A/4

DERWENT-CLASS: L03 M14 U11 U12

CPI-CODES: L04-E03A; M14-A04;

EPI-CODES: U11-C01A1; U11-C01J6; U11-C09A; U12-A01A1X; U12-A01A2; U12-B03C;

=> mov#####
L11 219617 MOV#####

=> d his

(FILE 'HOME' ENTERED AT 13:29:45 ON 22 JUN 2003)

FILE 'INSPEC' ENTERED AT 13:30:24 ON 22 JUN 2003

L1 13079 ELECTROLUMINESC#####
L2 607 ORGAN### (4A) EMISS####
L3 0 EVOPAR####
L4 54215 EVAPORA#####
L5 21091 MASK
L6 13551 L1 OR L2
L7 510 L4 AND L6
L8 6 L1 AND L2 AND L4
L9 5 L7 AND L5

FILE 'CA' ENTERED AT 13:33:52 ON 22 JUN 2003

L10 11 L9
L11 219617 MOV#####

=> l10 and l11
L12 0 L10 AND L11

=>

L10 ANSWER 1 OF 11 CA COPYRIGHT 2003 ACS

AN 138:330104 CA

TI Self-aligned hybrid deposition of organic materials through a **mask**
for fabricating an org. semiconductor device

IN Shtein, Max; Forrest, Stephen R.

PA The Trustees of Princeton University, USA

SO PCT Int. Appl., 79 pp.

CODEN: PIXXD2

DT Patent

LA English

IC ICM H01L021-00

ICS H01L051-40; H01L021-20

CC 76-3 (Electric Phenomena)

Section cross-reference(s): 52, 73, 75

FAN.CNT 2

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
	-----	---	-----	-----	-----
PI	WO 2003034471	A1	20030424	WO 2002-US28089	20020904
	W:				
	AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN,				
	CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,				
	GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR,				
	LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH,				
	PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TN, TR, TT, TZ,				
	UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, AM, AZ, BY, KG, KZ, MD, RU,				
	TJ, TM				
	RW:				
	GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AT, BE, BG,				
	CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL,				
	PT, SE, SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR,				
	NE, SN, TD, TG				
	US 2003087471	A1	20030508	US 2002-233482	20020904
PRAI	US 2001-316264P	P	20010904		
	US 2001-316968P	P	20010905		
	US 2001-332090P	P	20011121		
	US 2001-317215P	P	20010904		
AB	A 1st layer is deposited over a substrate through a mask by a 1st process that results in the 1st layer having a 1st area of coverage. A 2nd layer is then deposited over the substrate through the mask by a 2nd process that results in the 2nd layer having a 2nd area of coverage that is different from the 1st area of coverage.				
ST	hybrid deposition mask org semiconductor device fabrication				
IT	Electroluminescent devices				
	Semiconductor device fabrication				
	Solar cells				
	Transistors				
	Vapor deposition process				
	(org.; self-aligned hybrid deposition of org. materials through mask for fabricating org. semiconductor device)				
IT	Optical imaging devices				
	(self-aligned hybrid deposition of org. materials through mask for fabricating org. semiconductor device)				
IT	Evaporation				
	(vacuum, thermal; self-aligned hybrid deposition of org. materials through mask for fabricating org. semiconductor device)				
IT	2085-33-8, Alq3				
	RL: DEV (Device component use); FMU (Formation, unclassified); PEP (Physical, engineering or chemical process); PYP (Physical process); FORM (Formation, nonpreparative); PROC (Process); USES (Uses)				
	(self-aligned hybrid deposition of org. materials through mask for fabricating org. semiconductor device)				

RE.CNT 4 THERE ARE 4 CITED REFERENCES AVAILABLE FOR THIS RECORD

RE

(1) Burrows; US 6013538 A 2000 CAPLUS

(2) Isberg; US 5998085 A 1999 CA

- (3) Lee; US 20010005528 A 2001 CA
(4) Shieh; US 5641611 A 1997

L10 ANSWER 2 OF 11 CA COPYRIGHT 2003 ACS
AN 138:311677 CA
TI Method of **evaporating** thin film used in organic
electroluminescent display
IN Chung, Chia-Tin
PA Chi Mei Optoelectronics Corporation, Taiwan
SO U.S. Pat. Appl. Publ., 12 pp.
CODEN: USXXCO
DT Patent
LA English
IC ICM B05D005-12
ICS C23C016-00
NCL 427248100; 427058000
CC 74-13 (Radiation Chemistry, Photochemistry, and Photographic and Other
Reprographic Processes)
Section cross-reference(s): 73

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2003072876	A1	20030417	US 2002-55646	20020122
	JP 2003123970	A2	20030425	JP 2002-65628	20020311
PRAI	TW 2001-90125566	A	20011016		
AB	In evapg. thin film used in org. electroluminescent display, a mask having a plurality of openings is placed below a display substrate, and a plane evapn. source is placed below the mask . The plane evapn. source has a plurality of evapg. material cells which are resp. aligned to the openings of the mask . The evapg. material cells are evapd. to deposit a plurality of thin films on predetd. regions of the display substrate.				
ST	film evapg org electroluminescent display				
IT	Electroluminescent devices (displays; method of evapg. thin film used in org. electroluminescent display)				
IT	Luminescent screens Luminescent substances (electroluminescent ; method of evapg. thin film used in org. electroluminescent display)				
IT	Evaporation Films (method of evapg. thin film used in org. electroluminescent display)				

L10 ANSWER 3 OF 11 CA COPYRIGHT 2003 ACS
AN 138:228962 CA
TI **Evaporation** masks for organic **electroluminescent**
devices
IN Wakabayashi, Morimitsu
PA Japan
SO Jpn. Kokai Tokkyo Koho, 6 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
IC ICM H05B033-10
ICS C23C014-04; G09F009-00; G09F009-30; H05B033-12; H05B033-14
CC 73-5 (Optical, Electron, and Mass Spectroscopy and Other Related
Properties)

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2003077654	A2	20030314	JP 2001-265618	20010903
PRAI	JP 2001-265618		20010903		

AB The masks comprise a 1st and a 2nd patterned stripe coating **mask** attached to a substrate and to the adjacent layers including a red, a green and a blue phosphor layer.

ST evapn **mask** org **electroluminescent** device

IT Anodes
Cathodes
 Electroluminescent devices
 Evaporation
Luminescent substances
Phosphors
 (evapn. masks for org. **electroluminescent** devices)

IT 147-14-8, Copper phthalocyanine 2085-33-8, Tris(8-quinolinolato)aluminum 50926-11-9, ITO 65181-78-4, TPD 123847-85-8, NPB 124729-98-2, MTDATA
RL: DEV (Device component use); USES (Uses)
 (evapn. masks for org. **electroluminescent** devices)

L10 ANSWER 4 OF 11 CA COPYRIGHT 2003 ACS

AN 138:212904 CA

TI Method for manufacturing **electroluminescence** display panel and **evaporation mask**

IN Nishikawa, Ryuji; Yamada, Tsutomu

PA Japan

SO U.S. Pat. Appl. Publ., 10 pp.

CODEN: USXXCO

DT Patent

LA English

IC ICM B05D005-12

ICS C23C016-00; B05D001-32

NCL 427066000; 427068000; 427248100; 427282000

CC 74-13 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2003044516	A1	20030306	US 2002-231963	20020830
	CN 1404345	A	20030319	CN 2002-141467	20020830
	JP 2003157974	A2	20030530	JP 2002-252452	20020830
PRAI	JP 2001-264694	A	20010831		

AB An evapn. **mask** onto which an opening is formed for selectively allowing passage of an evapn. substance from an evapn. source onto a glass substrate to form an evapn. layer of an **electroluminescence** element in a predetd. pattern is placed between an evapn. source and a glass substrate and evapn. is performed. As a material for the evapn. **mask**, a material having a thermal expansion coeff. 160% or smaller of the thermal coeff. of glass is employed so as to minimize the thermal deformation of the evapn. **mask** which is closer the evapn. source and temp. of which is increased, to thereby improve the evapn. patterning precision.

ST **electroluminescence** display panel evapn **mask**
patterning

IT **Electroluminescent** devices
(displays; method for manufg. **electroluminescence** display panel and evapn. **mask**)

IT Luminescent screens
(**electroluminescent**; method for manufg. **electroluminescence** display panel and evapn. **mask**)

IT Lithography
Photomasks (lithographic masks)
Thin film transistors
(method for manufg. **electroluminescence** display panel and evapn. **mask**)

IT Glass, uses
RL: DEV (Device component use); USES (Uses)
(method for manufg. **electroluminescence** display panel and

evapn. mask)
 IT 11110-39-7, Iron 64, nickel 36 39362-79-3, 42 Alloy 99353-88-5
 RL: DEV (Device component use); PRP (Properties); USES (Uses)
 (method for manufg. electroluminescence display panel and
 evapn. mask)

L10 ANSWER 5 OF 11 CA COPYRIGHT 2003 ACS
 AN 138:189155 CA
 TI Manufacturing electroluminescence element and
 evaporation mask on a plastic
 IN Nishikawa, Ryuji; Yamada, Tsutomu
 PA Japan
 SO U.S. Pat. Appl. Publ., 8 pp.
 CODEN: USXXCO
 DT Patent
 LA English
 IC ICM B05D005-12
 ICS C23C016-00; B05D001-32
 NCL 427066000; 427248100; 427068000; 427282000
 CC 38-3 (Plastics Fabrication and Uses)
 Section cross-reference(s): 74, 76

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2003044517	A1	20030306	US 2002-232625	20020830
	CN 1404344	A	20030319	CN 2002-141466	20020830
	JP 2003151768	A2	20030523	JP 2002-252443	20020830
PRAI	JP 2001-264707	A	20010831		

AB An evapn. substance from the evapn. source is allowed to selectively pass through .gtoreq.1 openings formed on the evapn. mask corresponding to the pattern of an evapn. layer of an EL element, to form the evapn. layer on the plastic substrate. As the material for the evapn. mask, a material whose thermal expansion coeff. is similar to (within a range of .+-.30%) the thermal expansion coeff. of the plastic substrate, such as a polyimide, is employed. It is preferable to employ a material having a thermal endurance which is, for example, .gtorsim.50.degree. than the thermal endurance of the plastic substrate. By employing such a material for the evapn. mask, it is possible to ensure that the plastic substrate and the evapn. mask will exhibit the same degree of thermal deformation during evapn., enabling improvement in the precision of evapn. patterning.

ST electroluminescence display mask fabrication

IT Electroluminescent devices
 (displays; electroluminescence display mask on a polyimide substrate)

IT Electronic device fabrication
 (electroluminescence display mask on a polyimide substrate)

IT Luminescent screens
 (electroluminescent; electroluminescence display mask on a polyimide substrate)

IT Coating materials
 (masking; electroluminescence display mask on a polyimide substrate)

IT Plastics, uses
 Polyimides, uses
 RL: DEV (Device component use); USES (Uses)
 (substrate; electroluminescence display mask on a polyimide substrate)

IT 50926-11-9, ITO
 RL: DEV (Device component use); USES (Uses)
 (electrode; electroluminescence display mask on a polyimide substrate)

L10 ANSWER 6 OF 11 CA COPYRIGHT 2003 ACS
 AN 136:175511 CA
 TI Apparatus for **evaporating** a fluorescent material of a light emitting display device
 IN Ko, Yeong Uk; Ko, Ik Hwan; Sung, Un Cheol
 PA Hyundai Electronics Ind. Co., Ltd., S. Korea
 SO Repub. Korean Kongkae Taeho Kongbo, No pp. given
 CODEN: KRXXA7
 DT Patent
 LA Korean
 IC ICM H05B033-00
 CC 74-9 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	KR 2000039653	A	20000705	KR 1998-55054	19981215
PRAI	KR 1998-55054		19981215		

AB An app. for evapg. a fluorescent material for depositing in a light emitting displaying device is provided to reduce the no. of the processes which uses a **mask** by simultaneously evapg. the red, green, and blue fluorescent materials. Three fluorescent material supplying tubes are disposed at the upper portion of a transparent metal film. Red, green, and blue fluorescent bodies are located in the fluorescent material supplying tubes, resp. A plurality of nozzle holes are formed in the fluorescent material supplying tubes. The fluorescent material is injected through the nozzle holes. The fluorescent material supplying tubes is rotated from one side of the transparent metal film to the other side of the transparent metal film by a driving means.

ST vapor deposition app fluorescent material LED display
 IT **Electroluminescent** devices
 Fluorescent substances
 Vapor deposition apparatus
 (app. for evapg. a fluorescent material of a light emitting displaying device)

L10 ANSWER 7 OF 11 CA COPYRIGHT 2003 ACS
 AN 136:94638 CA
 TI Making encapsulated organic electronic devices
 IN McCormick, Fred B.; Baude, Paul F.; Vernstrom, George D.
 PA 3M Innovative Properties Company, USA
 SO PCT Int. Appl., 33 pp.
 CODEN: PIXXD2
 DT Patent
 LA English
 IC ICM H01L051-20
 ICS H01L051-40; H05B033-04
 CC 76-3 (Electric Phenomena)
 Section cross-reference(s): 38

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	WO 2002005361	A1	20020117	WO 2000-US31393	20001115
	W:				
	AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CR, CU, CZ, DE, DK, DM, DZ, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW, AM, AZ, BY, KG, KZ, MD, RU, TJ, TM				
	RW:				
	GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW, AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG				
	EP 1299913	A1	20030409	EP 2000-989200	20001115

R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,
IE, SI, LT, LV, FI, RO, MK, CY, AL, TR

PRAI US 2000-614993 A 20000712

WO 2000-US31393 W 20001115

AB The invention provides methods for making encapsulated org. electronic devices (OED) including org. LEDs (OLED). The present invention can provide a robust OED device by means of in situ edge sealing enhancing structural integrity and device lifetime. The edge sealing is provided by using an adhesive component applied to a substrate prior to OED element deposition. A thin layer of an adhesive (pressure sensitive adhesive, hot melt, or curable) is applied to release liner, openings are cut in the adhesive/liner composite, then the composite is adhered to an electrode-coated substrate. Alternatively, an adhesive may be applied directly onto the electrode-coated substrate, e.g., by printing in a desired pattern, optionally partially cured or dried, then covered with .gtoreq.1 liners that act as a **mask** during deposition of the OLED elements. Another method would be to prep. a blank liner with a patterned adhesive, then die cut openings complementary to the adhesive pattern in the liner to allow deposition of OLED elements once the adhesive/liner is placed on the substrate.

ST encapsulated org electronic device prepn

IT Electron beam **evaporation**

(alumina layer; making encapsulated org. electronic devices)

IT Siloxanes (nonpolymeric)

RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)

(coated on metal foil as adhesive-coated liner; making encapsulated org. electronic devices)

IT Polyesters, processes

RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)

(coated with siloxanes or fluorocarbons as adhesive-coated liner; making encapsulated org. electronic devices)

IT Adhesives

(conductive, thermal, elec.; making encapsulated org. electronic devices)

IT Adhesives

(curable; making encapsulated org. electronic devices)

IT Fluoropolymers, processes

RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)

(film as adhesive-coated liner; making encapsulated org. electronic devices)

IT Hydrocarbons, processes

RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)

(fluoro, coated on metal foil as adhesive-coated liner; making encapsulated org. electronic devices)

IT Electric contacts

Electroluminescent devices

Encapsulation

Lamps (nonelectric)

Microelectronic devices

Release coatings

Sealing

Shadow masks

(making encapsulated org. electronic devices)

IT Foils

(metal as protective layer; making encapsulated org. electronic devices)

IT Multilayers

(polymer as protective layer; making encapsulated org. electronic devices)

IT Films

(polymeric; making encapsulated org. electronic devices)

IT Adhesives
(pressure-sensitive; making encapsulated org. electronic devices)

IT Glass, uses
RL: DEV (Device component use); USES (Uses)
(thin flexible as protective layer; making encapsulated org. electronic devices)

IT 7789-24-4, Lithium fluoride, uses
RL: DEV (Device component use); USES (Uses)
(LiF/Al cathode; making encapsulated org. electronic devices)

IT 9003-07-0, Polypropylene
RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
(adhesive-coated liner; making encapsulated org. electronic devices)

IT 126213-51-2, Poly(ethylenedioxythiophene)
RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
(conductive polymer in light emitting construction; making encapsulated org. electronic devices)

IT 1314-13-2, Zinc oxide, uses 7429-90-5, Aluminum, uses 7439-93-2, Lithium, uses 7439-95-4, Magnesium, uses 7440-19-9, Samarium, uses 7440-22-4, Silver, uses 7440-39-3, Barium, uses 7440-57-5, Gold, uses 7440-65-5, Yttrium, uses 7440-70-2, Calcium, uses 50926-11-9, ITO 53740-87-7
RL: DEV (Device component use); USES (Uses)
(counter electrode; making encapsulated org. electronic devices)

IT 1344-28-1, Alumina, processes
RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
(electron beam evapn. on ITO; making encapsulated org. electronic devices)

IT 1332-29-2, Tin oxide
RL: DEV (Device component use); USES (Uses)
(fluorine, counter electrode; making encapsulated org. electronic devices)

IT 123847-85-8, .alpha.-NPD
RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
(hole transport layer in light emitting construction; making encapsulated org. electronic devices)

IT 147-14-8, Copper phthalocyanine 155306-71-1, C545T
RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
(in light emitting construction; making encapsulated org. electronic devices)

IT 2085-33-8, Tris(8-hydroxyquinolinato)aluminum
RL: DEV (Device component use); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
(light emitting layer; making encapsulated org. electronic devices)

RE.CNT 6 THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS RECORD
RE

- (1) Idemitsu Kosan Co; EP 0884930 A 1998 CA
- (2) Liu Youmin; US 5786664 A 1998 CA
- (3) Motorola Inc; EP 0762806 A 1997
- (4) Seiko Epson Corp; WO 0005929 A 2000 CA
- (5) Seiko Epson Corp; EP 1018857 A 2000 CA
- (6) Tdk Corp; EP 1021070 A 2000

L10 ANSWER 8 OF 11 CA COPYRIGHT 2003 ACS
AN 135:295947 CA
TI Manufacture of organic electroluminescence display
IN Yamada, Tsutomu
PA Sanyo Electric Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 7 pp.

CODEN: JKXXAF

DT Patent
LA Japanese
IC ICM H05B033-10
ICS C23C014-24; G09F009-00; H05B033-14
CC 73-5 (Optical, Electron, and Mass Spectroscopy and Other Related Properties)

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2001284046	A2	20011012	JP 2000-96094	20000331
	US 2001055844	A1	20011227	US 2001-820139	20010328
PRAI	JP 2000-96094	A	20000331		

AB The display comprises: (1) a glass substrate; (2) a pair of electrodes interposing an org. **electroluminescent** laminate; and (3) a switching and (4) a current-supplying TFT, where $h > nd$ (d and h = opening width and thickness of phosphor vaporization **mask**, resp.; $n = 1-2.5$).

ST org **electroluminescence** display vaporization **mask**

IT Thin film transistors

(TFT; manuf. of org. **electroluminescence** display)

IT Anodes

Cathodes

Electric switching

Evaporation